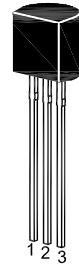


2SC2412

NPN Silicon Epitaxial Planar Transistor

for general purpose applications.

The transistor is subdivided into three groups Q, R and S, according to its DC current gain.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	7	V
Collector Current	I_C	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$ Current Gain Group	Q				
	R				
	S				
	h_{FE}	120	-	270	-
	h_{FE}	180	-	390	-
	h_{FE}	270	-	560	-
Collector Base Cutoff Current at $V_{CB} = 60\text{ V}$	I_{CBO}	-	-	0.1	μA
Emitter Base Cutoff Current at $V_{EB} = 7\text{ V}$	I_{EBO}	-	-	0.1	μA
Collector Base Breakdown Voltage at $I_C = 50\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E = 50\text{ }\mu\text{A}$	$V_{(BR)EBO}$	7	-	-	V
Collector Emitter Saturation Voltage at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	-	0.4	V
Gain Bandwidth Product at $V_{CE} = 12\text{ V}$, $-I_E = 2\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	180	-	MHz
Output Capacitance at $V_{CE} = 12\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	2	3.5	pF

